

ESH2PB, ESH2PC & ESH2PD

Vishay General Semiconductor

High Current Density Surface Mount Ultrafast Rectifiers

eSMP™ Series



DO-220AA (SMP)

MAJOR RATINGS AND CHARACTERISTICS					
I _{F(AV)}	2 A				
V_{RRM}	100 V, 150 V, 200 V				
t _{rr}	25 ns				
V_F at $I_F = 2 A$	0.75 V				
T _j max.	175 °C				

FEATURES

· Very low profile - typical height of 1.0 mm



- Ideal for automated placement
- · Glass passivated chip junction
- · Ultrafast recovery times for high frequency
- Low forward voltage drop, low power loss
- · Low thermal resistance
- Meets MSL level 1 per J-STD-020C, LF max peak of 260 °C
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

TYPICAL APPLICATIONS

For use in secondary rectification and free-wheeling for ultrafast switching speeds of ac-to-ac and dc-to-dc converters in high temperature conditions for both consumer and automotive applications.

MECHANICAL DATA

Case: DO-220AA (SMP)

Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per

J-STD-002B and JESD22-B102D

E3 suffix for commercial grade, HE3 suffix for high

reliability grade (AEC Q101 qualified)

Polarity: Color band denotes cathode end

MAXIMUM RATINGS (T _A = 25 °C unless otherwise noted)					
PARAMETER	SYMBOL	ESH2PB	ESH2PC	ESH2PD	UNIT
Device marking code		P2B	P2C	P2D	
Maximum repetitive peak reverse voltage	V_{RRM}	100	150	200	V
Maximum average forward rectified current (Fig. 1)	I _{F(AV)}	2.0			Α
Peak forward surge current 10 ms single half sine- wave superimposed on rated load	I _{FSM}	50			А
Operating junction and storage temperature range	T_J , T_{STG}	- 55 to + 175			°C

ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)					
PARAMETER	TEST CONDITIONS	SYMBOL	TYP.	MAX.	UNIT
Maximum instantaneous forward voltage ⁽¹⁾	at $I_F = 2 A$, $T_j = 25 °C$ at $I_F = 2 A$, $T_j = 125 °C$	V _F	0.90 0.75	0.98 0.82	V
Maximum reverse current (1)	at rated V_R $T_j = 25 ^{\circ}C$ $T_j = 125 ^{\circ}C$	I _R	0.2 12.6	1.0 25	μΑ
Maximum reverse recovery time	at $I_F = 0.5 \text{ A}$, $I_R = 1 \text{ A}$, $I_{rr} = 0.25 \text{ A}$	t _{rr}	-	25	ns

Document Number: 89016 www.vishay.com
Revision: 27-Jun-07 1

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ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)					
PARAMETER	TEST CONDITIONS SYME		TYP.	MAX.	UNIT
Typical reverse recovery time	$\begin{array}{l} \text{at } I_F = 1.0 \text{ A, } V_R = 30 \text{ V di/dt} = 50 \text{ A/}\mu\text{s,} \\ I_{rr} = 10 \% I_{RM} T_j = 25 \ ^{\circ}\text{C} \\ \text{at } I_F = 1.0 \text{ A, } V_R = 30 \text{ V di/dt} = 50 \text{ A/}\mu\text{s,} \\ I_{rr} = 10 \% I_{RM} T_j = 100 \ ^{\circ}\text{C} \end{array}$	t _{rr}	1 1	25 35	ns
Typical stored charge	$\begin{array}{l} \text{at } I_F = 1.0 \text{ A, } V_R = 30 \text{ V di/dt} = 50 \text{ A/}\mu\text{s,} \\ I_{rr} = 10 \% I_{RM} T_j = 25 \ ^{\circ}\text{C} \\ \text{at } I_F = 1.0 \text{ A, } V_R = 30 \text{ V di/dt} = 50 \text{ A/}\mu\text{s,} \\ I_{rr} = 10 \% I_{RM} T_j = 100 \ ^{\circ}\text{C} \end{array}$	Q _{rr}		10 15	nC
Typical junction capacitance	at 4.0 V, 1 MHz	CJ	-	25	pF

Note:

(1) Pulse test: 300 µs pulse width, 1 % duty cycle

THERMAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)						
PARAMETER	SYMBOL	ESH2PB	ESH2PC	ESH2PD	UNIT	
Typical thermal resistance ⁽¹⁾	$egin{array}{l} R_{ hetaJA} \ R_{ hetaJL} \ R_{ hetaJC} \end{array}$	80 15 22		°C/W		

Note:

(1) Thermal resistance from junction to ambient and junction to lead mounted on P.C.B. with 6.0 x 6.0 mm copper pad areas. $R_{\theta JL}$ is measured at the terminal of cathode band. $R_{\theta JC}$ is measured at the top centre of the body

ORDERING INFORMATION (Example)						
PREFERRED P/N	UNIT WEIGHT (g)	PREFERRED PACKAGE CODE	BASE QUANTITY	DELIVERY MODE		
ESH2PB-E3/84A	0.024	84A	3000	7" Diameter Plastic Tape & Reel		
ESH2PB-E3/85A	0.024	85A	10000	13" Diameter Plastic Tape & Reel		
ESH2PBHE3/84A (1)	0.024	84A	3000	7" Diameter Plastic Tape & Reel		
ESH2PBHE3/85A (1)	0.024	85A	10000	13" Diameter Plastic Tape & Reel		

Note:

(1) Automotive grade AEC Q101 qualified

RATINGS AND CHARACTERISTICS CURVES

(T_A = 25 °C unless otherwise noted)

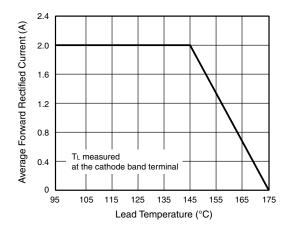


Figure 1. Forward Current Derating Curve

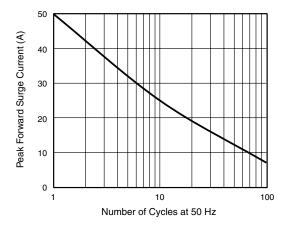


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current



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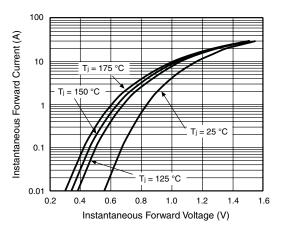


Figure 3. Typical Instantaneous Forward Characteristics

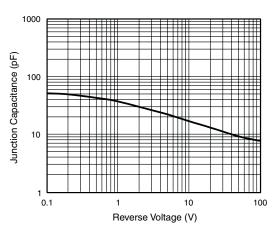


Figure 5. Typical Junction Capacitance

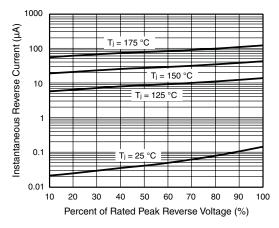
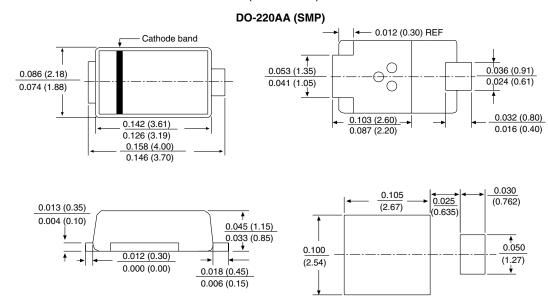


Figure 4. Typical Reverse Leakage Characteristics

PACKAGE OUTLINE DIMENSIONS in inches (millimeters)



Document Number: 89016 Revision: 27-Jun-07 www.vishay.com

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Document Number: 91000 www.vishay.com
Revision: 08-Apr-05 1